

**AMENDMENTS TO THE CLAIMS:**

Please cancel claims 14-31 and 48-88, without prejudice, and add new claims 95-106, as shown below.

This listing of claims will replace all prior versions and listings of claims in the Application:

**Claim 1 (original):** An organic insulating film formed using, as a source, a polyorganosilane whose C/Si ratio is at least equal to or greater than 5 and, at the same time, molecular weight is equal to or greater than 100.

**Claim 2 (original):** An organic insulating film according to Claim 1, wherein said polyorganosilane is one or more types of polyorganosilanes selected from the group consisting of trimethylvinylsilane, triethylvinylsilane, dimethyldivinylsilane, diethyldivinylsilane, methyltrivinylsilane, ethyltrivinylsilane, tetravinylsilane, tetraethylsilane and triethylsilane.

**Claim 3 (original):** An organic insulating film according to Claim 1, wherein said polyorganosilane contains a vinyl group, at least, in a part thereof.

**Claim 4 (original):** An organic insulating film according to Claim 3, wherein said polyorganosilane containing a vinyl group, at least, in a part thereof is one or more types of polyorganosilanes selected from the group consisting of trimethylvinylsilane, triethylvinylsilane, dimethyldivinylsilane, diethyldivinylsilane, methyltrivinylsilane, ethyltrivinylsilane and tetravinylsilane.

**Claim 5 (original):** An organic insulating film according to Claim 1, wherein a C=C bond is contained.

**Claim 6 (original):** An organic insulating film according to Claim 5, wherein a vinyl group is contained.

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**Claim 7 (currently amended):** An organic insulating film according to ~~one of Claims~~  
Claim 1, wherein said organic insulating film is one selected from the group consisting of a  
SiCH film, a SiCHN film and a SiOCH film.

**Claim 8 (original):** An organic insulating film according to Claim 7, wherein said SiCH film  
is composed of Si, C and H elements and a C/Si composition ratio thereof is not less than 0.9.

**Claim 9 (original):** An organic insulating film according to Claim 8, wherein said SiCH film  
has a density of less than  $1.4 \text{ g / cm}^3$ .

**Claim 10 (original):** An organic insulating film according to Claim 7, wherein said SiCHN  
film is composed of Si, C, H and N elements and a C/Si composition ratio thereof is not less  
than 1.0.

**Claim 11 (original):** An organic insulating film according to Claim 10, wherein said SiCHN  
film has a density of less than  $1.6 \text{ g / cm}^3$ .

**Claim 12 (original):** An organic insulating film according to Claim 7, wherein said SiOCH  
film is composed of, at least, Si, C, O and H elements and a C/Si composition ratio thereof is  
not less than 0.8.

**Claim 13 (original):** An organic insulating film according to Claim 12, wherein said SiOCH  
film has a density of less than  $1.2 \text{ g / cm}^3$ .

**Claims 14-31 (canceled)**

**Claim 32 (original):** A semiconductor device comprising, at least, one insulating film selected  
from the group consisting of an interlayer insulating film, an etching stopper film and a barrier  
insulating film against a metal; wherein

said interlayer insulating film, etching stopper film or barrier insulating film against a  
metal is an organic insulating film; wherein

said organic insulating film formed using, as a source, a polyorganosilane whose C/Si ratio is at least equal to or greater than 5 and, at the same time, molecular weight is equal to or greater than 100.

**Claim 33 (original):** A semiconductor device according to Claim 32, which comprises a trench interconnection structure.

**Claim 34 (original):** A semiconductor device having a trench interconnection structure, which comprises a first insulating film formed on a semiconductor substrate, a first trench interconnection formed in said first insulating film, a second insulating film, a third insulating film, a second trench interconnection formed in said third insulating film, a via plug that is formed in said second insulating film and connects said first trench interconnection with said second trench interconnection; wherein

at least said first insulating film, said second insulating film and said third insulating film are each made of a SiOCH film as set forth in Claim 7.

**Claim 35 (original):** A semiconductor device according to Claim 34, wherein said first insulating film is a layered film made of said SiOCH film and a hard mask film.

**Claim 36 (original):** A semiconductor device according to Claim 34; wherein

said first insulating film is a layered film made of an etching stopper film, said SiOCH film and a hard mask film; and

said etching stopper film is either of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 37 (original):** A semiconductor device according to Claim 34; wherein

said second insulating film is a layered film made of a barrier insulating film, a SiOCH film as set forth in Claim 7 and a hard mask film; and

said barrier insulating film is either of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 38 (original):** A semiconductor device according to Claim 34; wherein

said second insulating film is a layered film made of a barrier insulating film and said SiOCH film; and

said barrier insulating film is either of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 39 (original):** A semiconductor device according to Claim 34; wherein

said second insulating film is a layered film made of a barrier insulating film, said SiOCH film and an etching stopper film; and

each of said barrier insulating film and said etching stopper film is either of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 40 (original):** A semiconductor device according to Claim 34, wherein said third insulating film is a layered film made of said SiOCH film and a hard mask film.

**Claim 41 (original):** A semiconductor device according to Claim 34; wherein

said third insulating film is a layered film made of an etching stopper film, said SiOCH film and a hard mask film; and

said etching stopper film is either of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 42 (original):** A semiconductor device according to Claim 34; wherein

a top section of said second trench interconnection is covered with a barrier insulating film; and

said barrier insulating film is either of a SiCH film and a SiCHN film as set forth in

Claim 7.

**Claim 43 (previously presented):** A semiconductor device according to Claim 36, wherein said etching stopper film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 44 (previously presented):** A semiconductor device according to Claim 37, wherein said barrier insulating film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 45 (original):** A semiconductor device according to Claim 34, wherein, at least, one of said trench interconnection and said via plug is formed of a copper containing metal.

**Claim 46 (original):** A semiconductor device according to Claim 45, wherein said copper containing metal further contains one or more metals selected from the group consisting of Si, Al, Ag, W, Mg, Be, Zn, Pd, Cd, Au, Hg, Pt, Zr, Ti, Sn, Ni and Fe.

**Claim 47 (original):** A semiconductor device according to Claim 34, wherein said trench interconnection and said via plug each comprise one or more barrier metal layers selected from the group consisting of layers of Ti, TiN, TiSiN, Ta, TaN and TaSiN.

**Claim 48-88 (canceled)**

**Claim 89 (previously presented):** A semiconductor device according to Claim 36, wherein said etching stopper film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 90 (previously presented):** A semiconductor device according to Claim 39, wherein said etching stopper film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 91 (previously presented):** A semiconductor device according to Claim 41, wherein said etching stopper film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 92 (previously presented):** A semiconductor device according to Claim 38, wherein said barrier insulating film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 93 (previously presented):** A semiconductor device according to Claim 39, wherein said barrier insulating film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 94 (previously presented):** A semiconductor device according to Claim 42, wherein said barrier insulating film is a layered film made of a SiCH film and a SiCHN film as set forth in Claim 7.

**Claim 95 (new):** An organic insulating film comprising: a SiCHN film with a C/Si composition ratio of from 1.0 to 1.3.

**Claim 96 (new):** An organic insulating film according to claim 95, wherein said SiCHN film has a density equal to or less than  $1.6 \text{ g / cm}^3$ .

**Claim 97 (new):** An organic insulating film according to claim 95, wherein said SiCHN film has a C=C bond contained therein.

**Claim 98 (new):** An organic insulating film according to claim 95, wherein said SiCHN film has a density equal to or less than  $1.6 \text{ g / cm}^3$  and a C=C bond contained therein.

**Claim 99 (new):** An organic insulating film comprising: a SiCH film with a C/Si composition ratio of from 0.9 to 1.3.

**Claim 100 (new):** An organic insulating film according to claim 99, wherein said SiCHN film has a density equal to or less than  $1.4 \text{ g / cm}^3$ .

**Claim 101 (new):** An organic insulating film according to claim 99, wherein said SiCH film has a C=C bond contained therein.

**Claim 102 (new):** An organic insulating film according to claim 99, wherein said SiCH film has a density equal to or less than  $1.4 \text{ g / cm}^3$  and a C=C bond contained therein.

**Claim 103 (new):** An organic insulating film comprising: a SiOCH film with a C/Si composition ratio of from 0.8 to 1.3.

**Claim 104 (new):** An organic insulating film according to claim 103, wherein said SiOCH film has a density equal to or less than  $1.2 \text{ g / cm}^3$ .

**Claim 105 (new):** An organic insulating film according to claim 103, wherein said SiOCH film has a C=C bond contained therein.

**Claim 106 (new):** An organic insulating film according to claim 103, wherein said SiOCH film has a density equal to or less than  $1.2 \text{ g / cm}^3$  and a C=C bond contained therein.